
2SK1159, 2SK1160

Silicon N-Channel MOS FET

HITACHI

Application

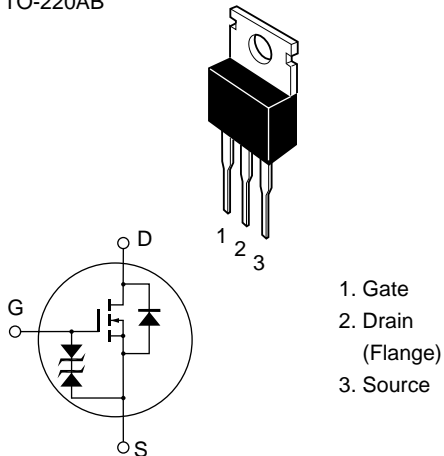
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and motor driver

Outline

TO-220AB



2SK1159, 2SK1160

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated	Unit
Drain to source voltage	2SK1159	V_{DSS}	450	V
	2SK1160		500	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	8	A
Drain peak current		$I_{D(pulse)}^{*1}$	32	A
Body to drain diode reverse drain current		I_{DR}	8	A
Channel dissipation		P_{ch}^{*2}	60	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

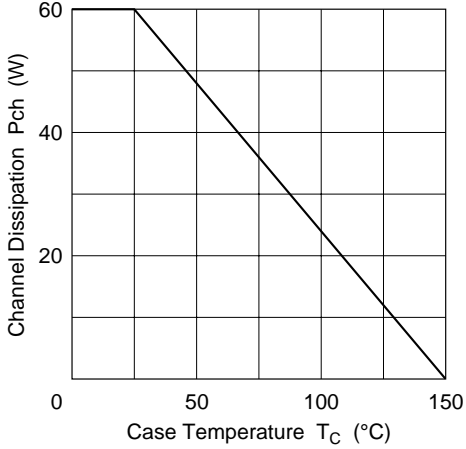
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

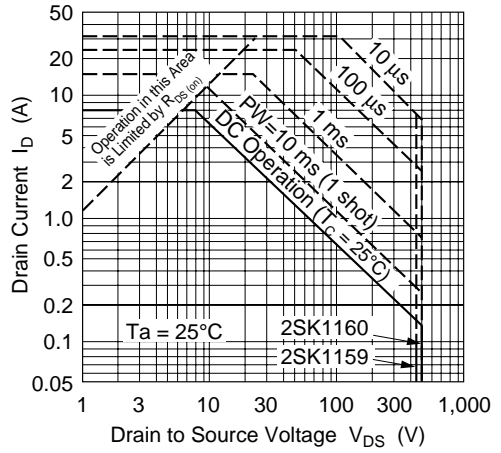
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK1159 $V_{(BR)DSS}$ 2SK1160	450 500	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	2SK1159 I_{DSS} 2SK1160	—	—	250	μA	$V_{DS} = 360 \text{ V}, V_{GS} = 0$ $V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	2SK1159 $R_{DS(on)}$ 2SK1160	—	0.55 0.60	0.7 0.8	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	4.5	7.5	—	S	$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	—	1150	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	—	340	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	Crss	—	55	—	pF	
Turn-on delay time	$t_{d(on)}$	—	17	—	ns	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	55	—	ns	$R_L = 7.5 \Omega$
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	t_f	—	45	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 8 \text{ A}, V_{GS} = 0$
Body to drain diode forward voltage	t_{rr}	—	350	—	ns	$I_F = 8 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Note: 1. Pulse test

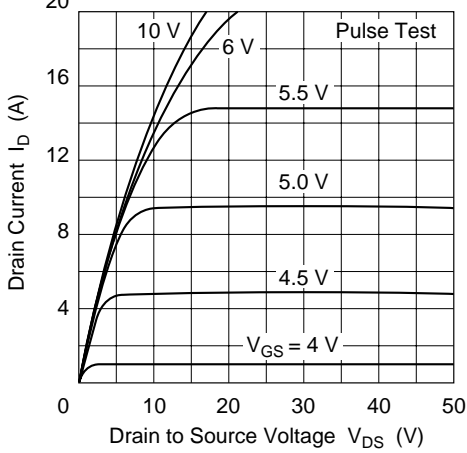
Power vs. Temperature Derating



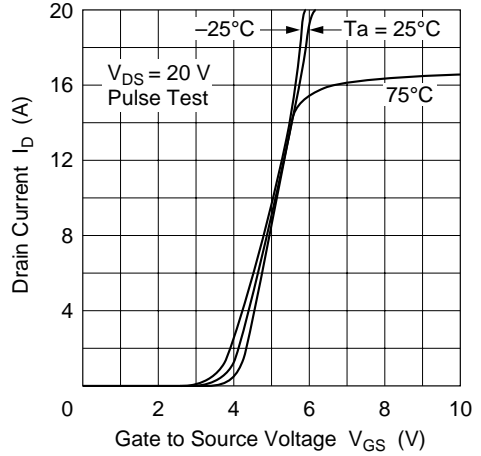
Maximum Safe Operation Area

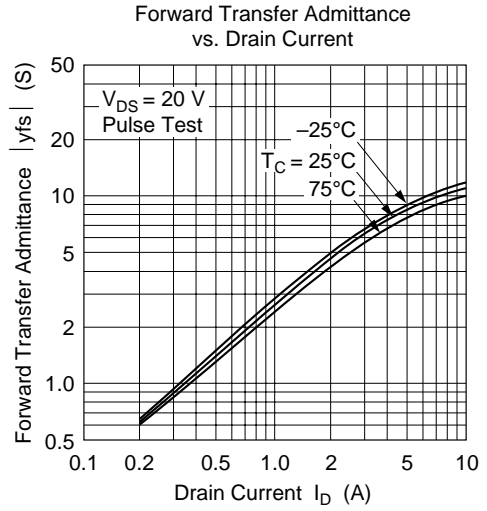
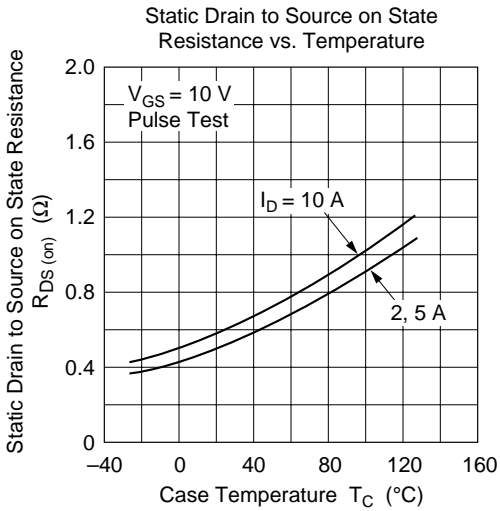
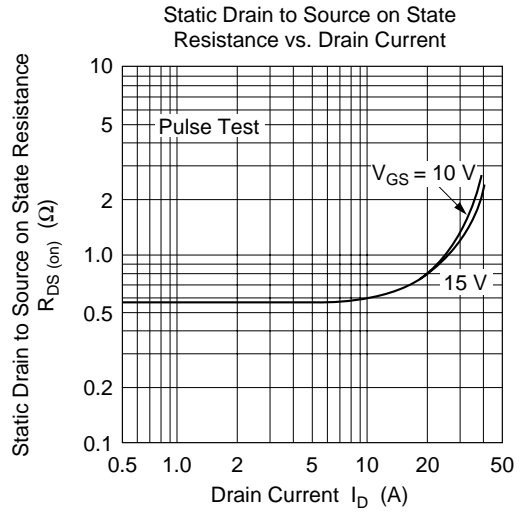
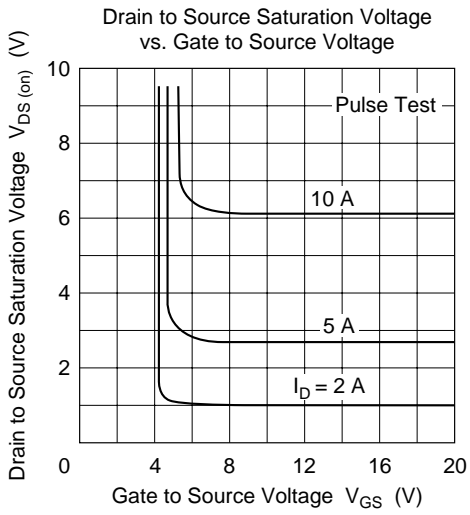


Typical Output Characteristics

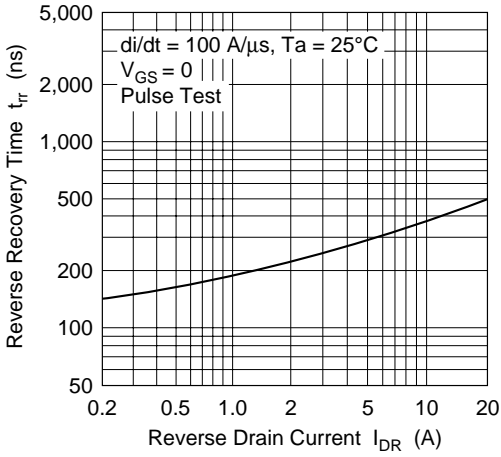


Typical Transfer Characteristics

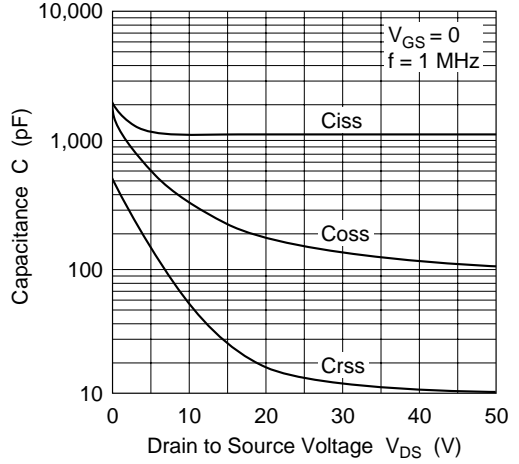




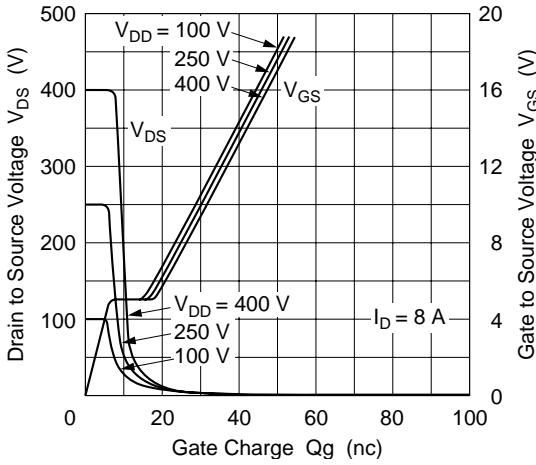
Body to Drain Diode Reverse Recovery Time



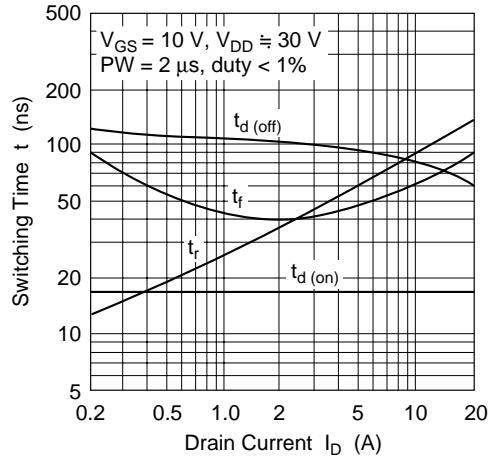
Typical Capacitance vs. Drain to Source Voltage

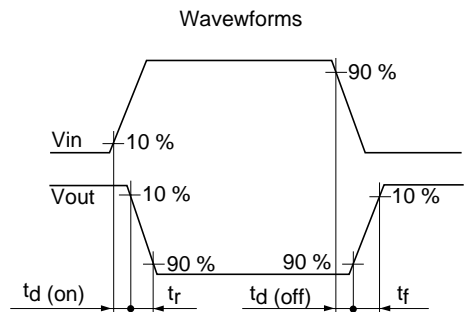
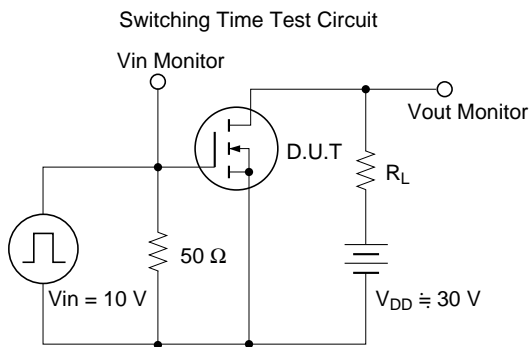
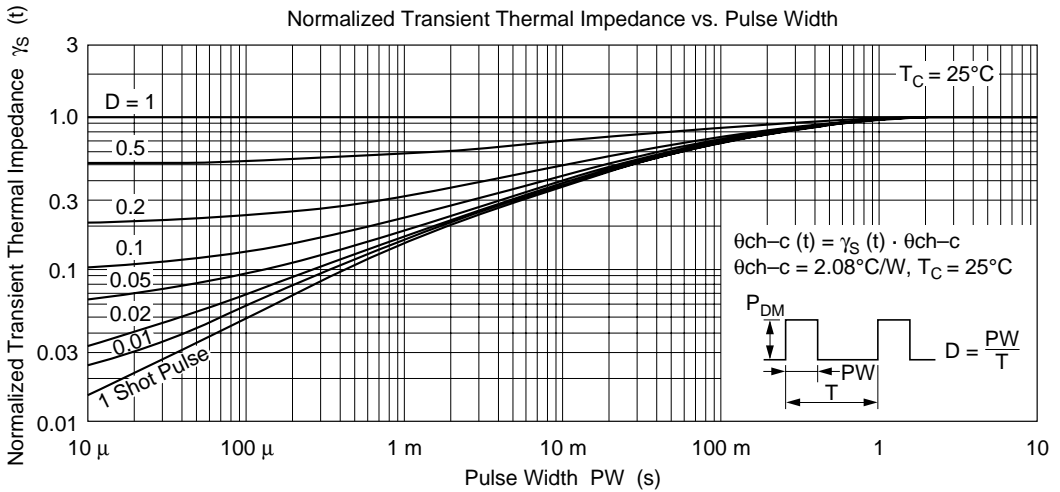
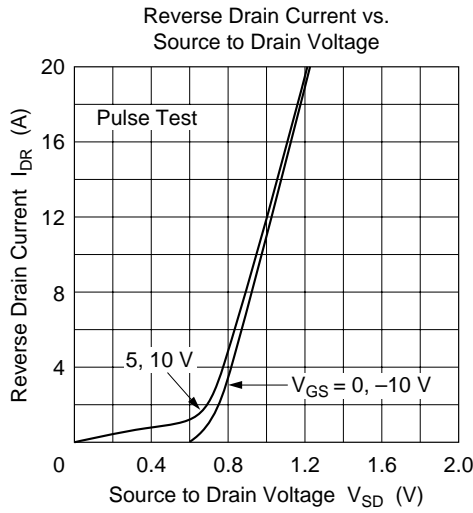


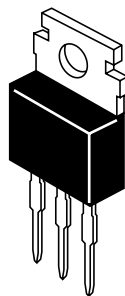
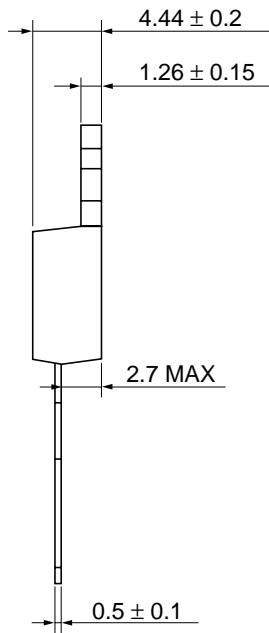
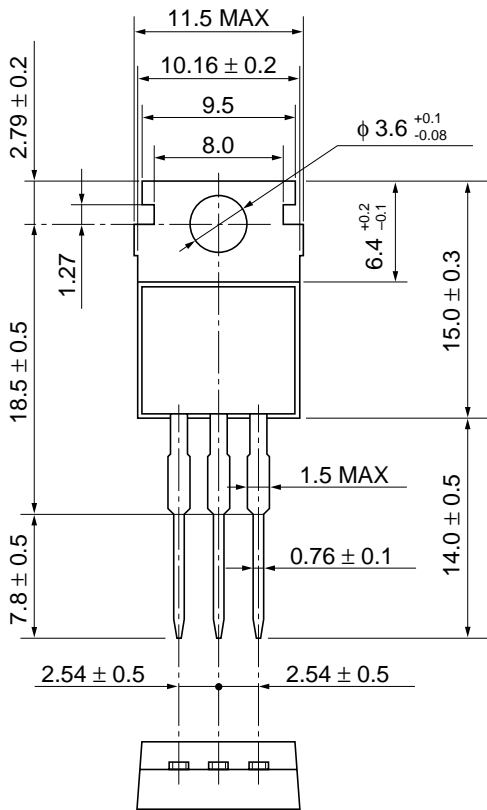
Dynamic Input Characteristics



Switching Characteristics







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

Cautions

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